

<b>Notice of References Cited</b>		Application/Control No.	Applicant(s)/Patent Under Reexamination	
		10/006,704	TRAPP, SHANE J.	
		Examiner	Art Unit	Page 1 of 1
		Lynette T. Umez-Eronini	1765	

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,015,761	01-2000	Merry et al.	438/727
	B	US-5,935,877	08-1999	Autryve, Luc Van	438/743
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

**FOREIGN PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP 54054578A	04-1979	Japan	Yamagishi et al.	H01L 21/302
	O					
	P					
	Q					
	R					
	S					
	T					

**NON-PATENT DOCUMENTS**

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Yamagishi et al., Gas Plasma Etching Method, April 29, 1979, English Abstract of JP 54054578 A, 3 pages.
	V	Smolinsky et al., Reactive Ion Etching of Silicon Oxides with Ammonia and Trifluoromethane. The Role of Nitrogen in the Discharge, J. Electrochem. Soc.: SOLID-STATE SCIENCE AND TECHNOLOGY, No. 5, Vol. 129, May 1982, pp. 1036-1039.
	W	
	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.